IN THE CLAIMS

- 1-12. (Canceled).
- 13. (Currently Amended) A method for megasonic cleaning of semiconductor wafers5 comprising the steps of:

generating two or more parallel megasonic waves in a cleaning fluid, the megasonic waves having a common direction of travel;

immersing the wafers in the cleaning fluid; and

moving the wafers in the cleaning fluid through two or more of said megasonic waves in a direction that is generally perpendicular to the direction of travel of the megasonic waves and generally perpendicular to a plane parallel with the megasonic waves.

- 14. (Currently Amended) The method of claim 13 wherein the megasonic waves are
 generated across parallel regions of the fluid and the step of moving the wafers comprises reciprocating the wafers through at least two of said parallel regions.
 - 15-26. (Canceled).
- 20 27. (*Currently Amended*) A method for megasonic cleaning of semiconductor wafers comprising the steps of:

generating two or more parallel megasonic waves in a cleaning fluid; immersing the wafers in the cleaning fluid such that faces of the wafers are parallel with the waves; and

- moving the wafers in the cleaning fluid through said megasonic waves in a direction that is generally perpendicular to the megasonic waves and generally perpendicular to the faces of the wafers.
- 28. (New) The method of claim 13 wherein the megasonic waves are generated at the bottom of a reservoir holding the cleaning fluid and travel toward the top of the fluid and

the wafers are inserted vertically at the top of the fluid until they are covered with fluid and the wafers are reciprocated horizontally while covered with fluid.

29. (New) The method of claim 27 wherein the megasonic waves are generated at the
5 bottom of a reservoir holding the cleaning fluid and travel toward the top of the fluid and the wafers are inserted vertically at the top of the fluid until they are covered with fluid and the wafers are reciprocated horizontally while covered with fluid.